

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

GreenMOS[®]



Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

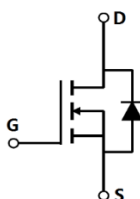
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	800	V
I_D , pulse	24	A
$R_{DS(ON)}$, max @ $V_{GS}=10V$	650	m Ω
Q_g	12.1	nC

Marking Information

Product Name	Package	Marking
OSG80R650DF	TO252	OSG80R650D

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	800	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	8	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		5	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, \text{pulse}}$	24	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	8	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, \text{pulse}}$	24	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	83	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	240	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\ldots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\ldots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	1.5	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	800			V	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		0.55	0.65	Ω	$V_{GS}=10\text{ V}$, $I_D=4\text{ A}$
			1.48			$V_{GS}=10\text{ V}$, $I_D=4\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			10	μA	$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		709.1		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}		44.8		pF	
Reverse transfer capacitance	C_{rss}		2		pF	
Turn-on delay time	$t_{d(on)}$		25.1		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=25\ \Omega$, $I_D=4\text{ A}$
Rise time	t_r		11.4		ns	
Turn-off delay time	$t_{d(off)}$		43.5		ns	
Fall time	t_f		25.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		12.1		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=4\text{ A}$
Gate-source charge	Q_{gs}		3.3		nC	
Gate-drain charge	Q_{gd}		4.2		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=8\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		193.7		ns	$V_R=400\text{ V}$, $I_S=4\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		1.7		μC	
Peak reverse recovery current	I_{rrm}		15.3		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=20\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

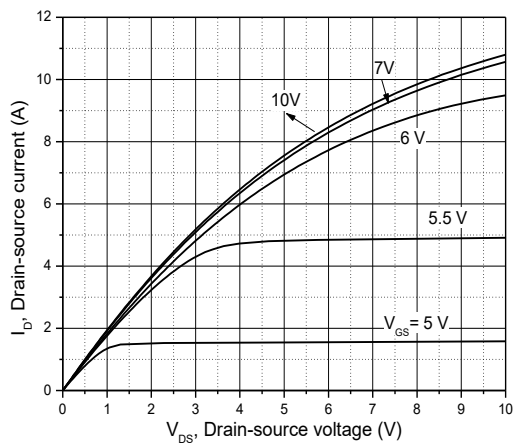


Figure 1. Typ. output characteristics

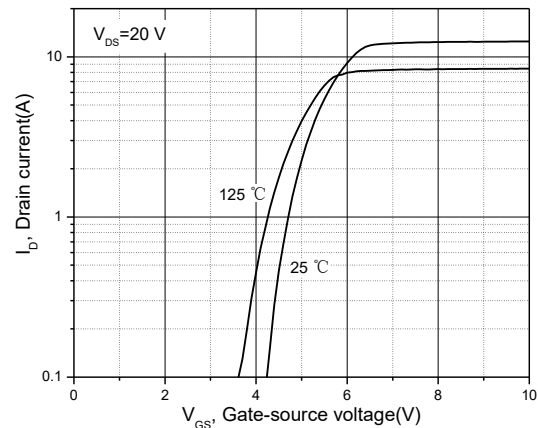


Figure 2. Typ. transfer characteristics

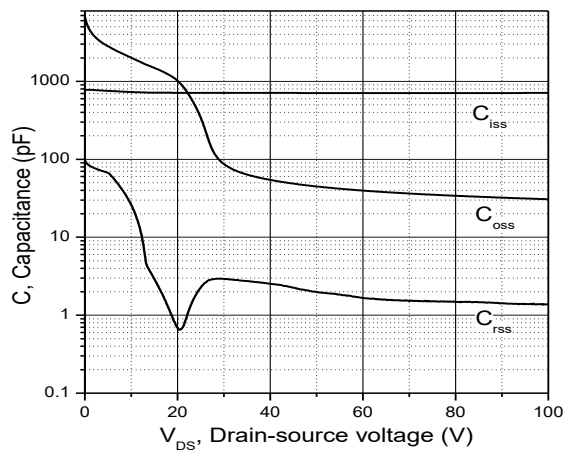


Figure 3. Typ. capacitances

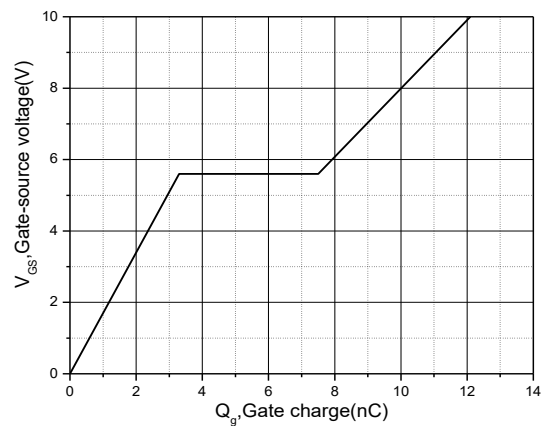


Figure 4. Typ. gate charge

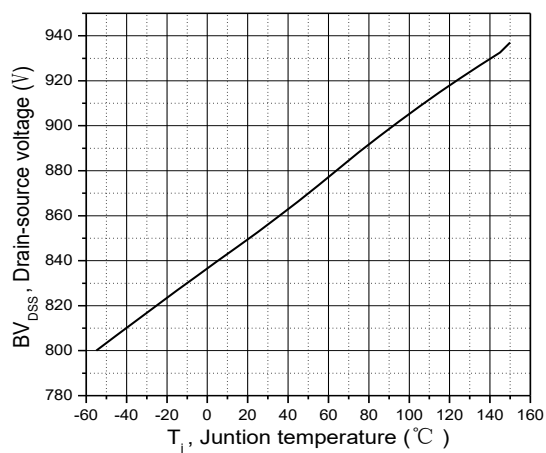


Figure 5. Drain-source breakdown voltage

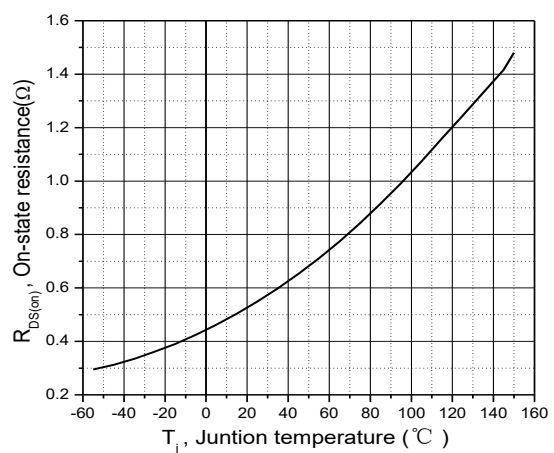


Figure 6. Drain-source on-state resistance

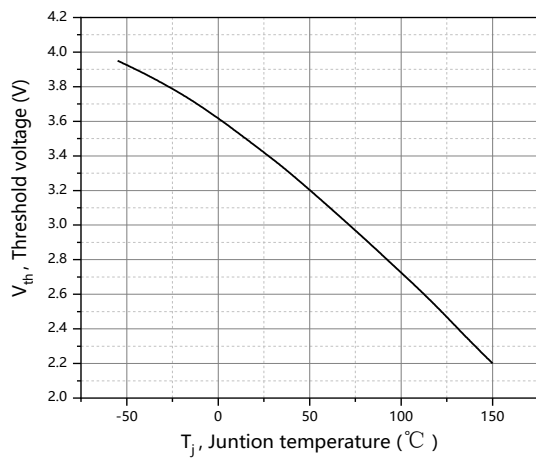


Figure 7. Threshold voltage

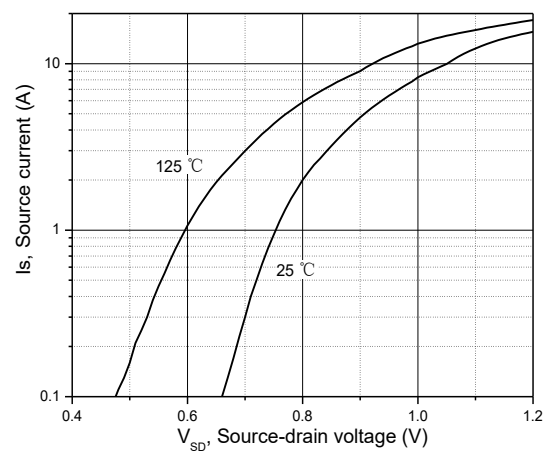


Figure 8. Forward characteristic of body diode

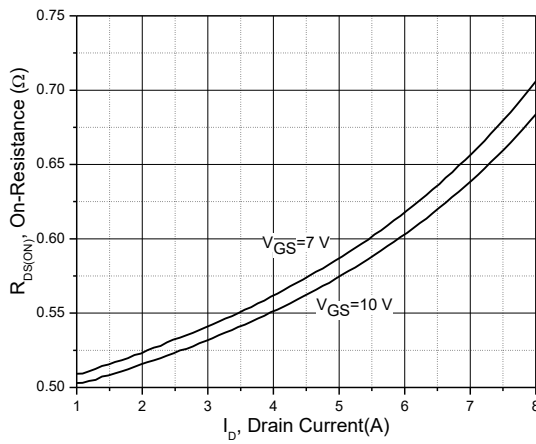


Figure 9. Drain-source on-state resistance

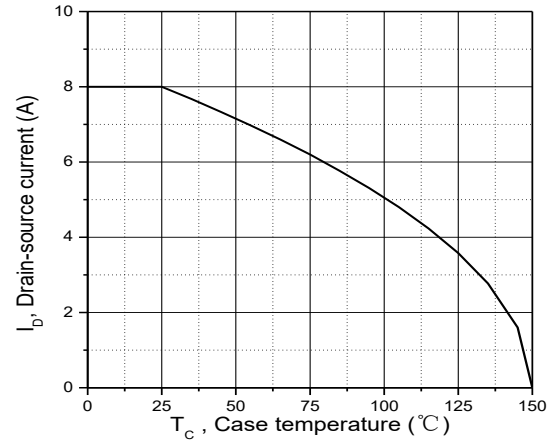


Figure 10. Drain current

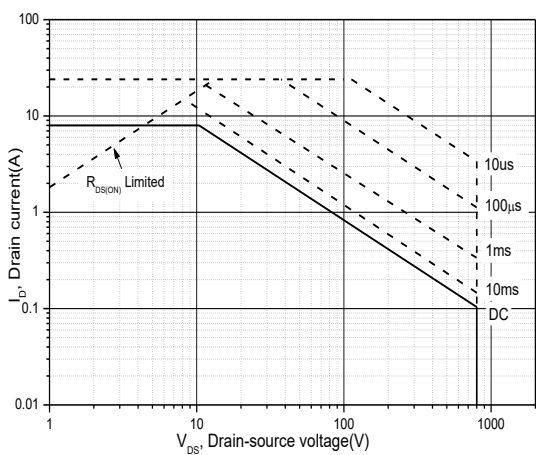


Figure 11. Safe operation area $T_C=25^\circ\text{C}$

Test circuits and waveforms

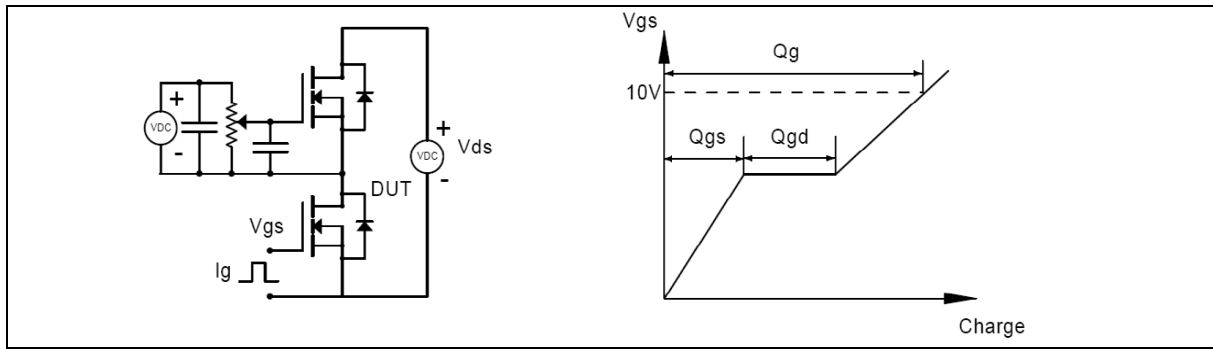


Figure 1. Gate charge test circuit & waveform

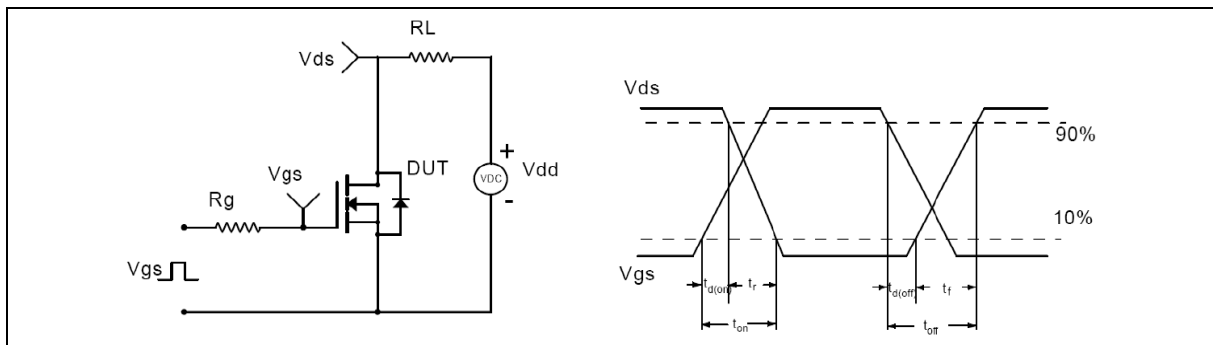


Figure 2. Switching time test circuit & waveforms

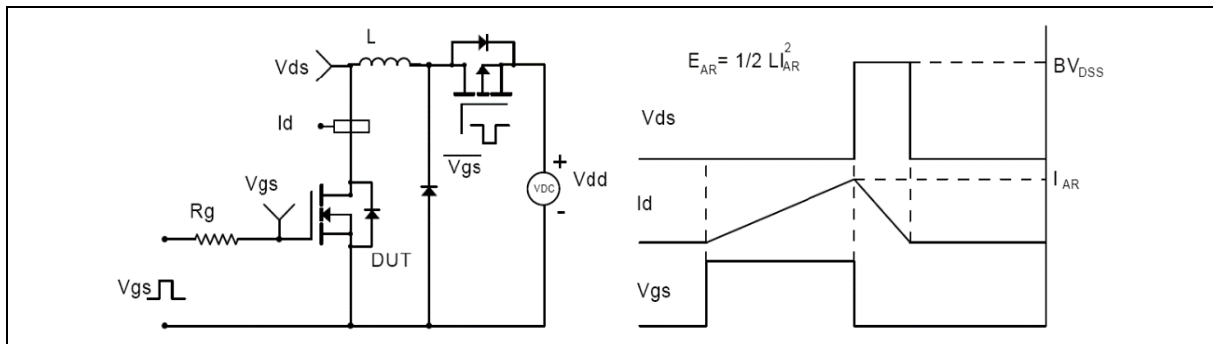


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

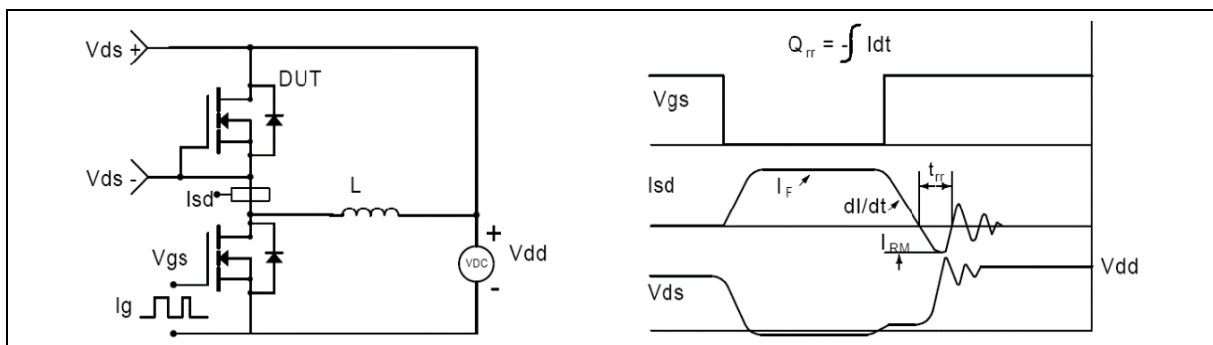
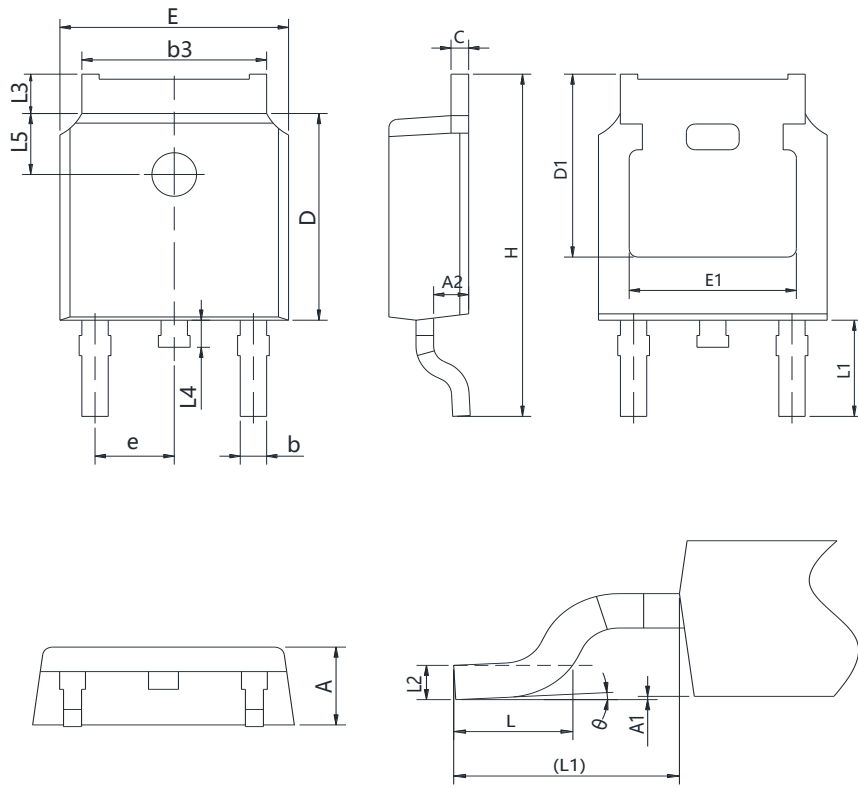


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
θ	0°	-	8°

Version 1: TO252-P package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO252-P	2500	2	5000	5	25000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG80R650DF	TO252	yes	yes	yes

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Oriental Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

For further information on technology, delivery terms and conditions and prices, please contact the Oriental Semiconductor sales representatives (www.orientalsemi.com).

© Oriental Semiconductor Co.,Ltd. All Rights Reserved 